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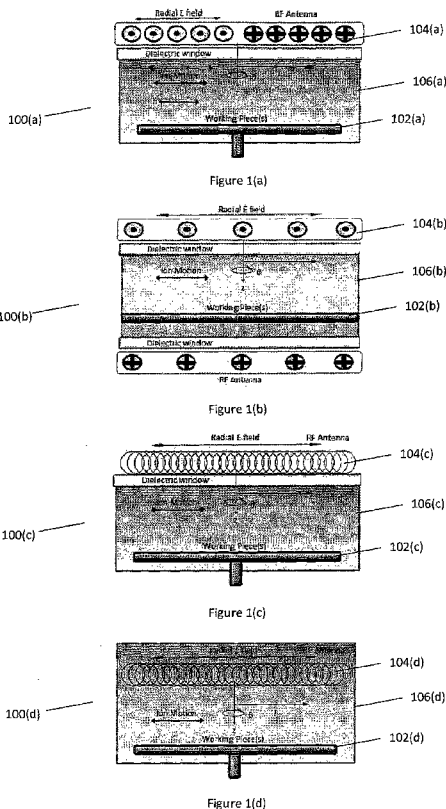
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(54) Title: A CAPACITIVELY COUPLED ELECTRODELESS PLASMA APPARATUS AND A METHOD USING CAPACITIVELY COUPLED ELECTRODELESS PLASMA FOR PROCESSING A SILICON SUBSTRATE



(57) Abstract: There is provided a capacitive coupled electrodeless plasma apparatus for processing a silicon substrate. The apparatus includes at least one inductive antenna driven by time-varying power sources for providing at least one electrostatic field; and a chamber for locating the silicon substrate. There is also provided a method for processing a silicon substrate using capacitively coupled electrodeless plasma.



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